DATA SHEET

Part No.	AN26218A
Package Code No.	XLGA011-W-1216AKA

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AN26218A

UMTS triple band LNA-IC

Overview

- AN26218A is LNA-IC for 800 MHz / 1.7 GHz / 2.1 GHz Band Applications.
- Realizing high performance by using 0.18 µm SiGeC Bi-CMOS process(fT = 90 GHz, fmax = 140 GHz).
- Each band is selectable and High/Low Gain-mode is changeable, controlled by integrated CMOS logic circuit.
- Achieving miniaturization by using small size package.

■ Features

- i catares			
 Low voltage operation 	+2.8 V typ.		
• Low current consumption	3.3 mA typ.		(High-Gain mode)
	11 μA typ.	2.1 GHz	(Low-Gain mode)
	25 μA typ.	800 MHz / 1.7 GHz	(Low-Gain mode)
High gain(Gain)	16.7 dB typ.	fRX = 2140 MHz	(High-Gain mode)
	16.7 dB typ.	fRX = 884.5 MHz	(High-Gain mode)
	16.5 dB typ.	fRX = 1862.5 MHz	(High-Gain mode)
Low noise figure(NF)	1.75 dB typ.	fRX = 2140 MHz	(High-Gain mode)
	1.80 dB typ.	fRX = 884.5 MHz	(High-Gain mode)
	1.65 dB typ.	fRX = 1862.5 MHz	(High-Gain mode)
 Low distortion 	0.0 dBm typ.	fRX = 2140 MHz	(High-Gain mode)
(IIP3 +10 MHz offset)	−5.0 dBm typ.	fRX = 884.5 MHz	(High-Gain mode)
	−3.0 dBm typ.	fRX = 1862.5 MHz	(High-Gain mode)

[•] Small package(WLCSP)

■ Applications

• UMTS triple-band handset

■ Package

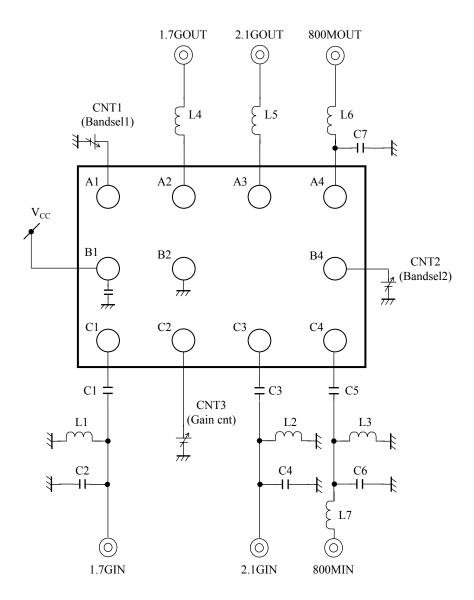
• 11 pin Wafer level chip size package (WLCSP) Size: 1.16 mm × 1.56 mm (0.4 mm pitch)

■ Туре

• Bi-CMOS IC

■ Application Circuit Example (Block Diagram)

(Top View)



- Notes) This application circuit is an example. The operation of mass production set is not guaranteed. You should perform enough evaluation and verification on the design of mass production set. You are fully responsible for the incorporation of the above application circuit and information in the design of your equipment.
 - This block diagram is for explaining functions. Part of the block diagram may be omitted, or it may be simplified.
 - External components : See page 29.

■ Pin Descriptions

Pin No.	Pin name	Туре	Description
A1	CNT1	Input	Band Selective SW1
A2	OUT1	Output	1.7 GHz RF Output
A3	OUT2	Output	2.1 GHz RF Output
A4	OUT3	Output	800 MHz RF Output
В1	V _{CC}	Power Supply	V_{CC}
B2	GND	Ground	GND
B4	CNT2	Input	Band Selective SW2
C1	IN1	Input	1.7 GHz RF Input
C2	CNT3	Input	High-Gain / Low-Gain Selective SW
C3	IN2	Input	2.1 GHz RF Input
C4	IN3	Input	800 MHz RF Input

■ Absolute Maximum Ratings

Note) Absolute maximum ratings are limit values which do not result in damages to this IC, and IC operation is not guaranteed at these limit values.

A No.	Parameter	Symbol	Rating	Unit	Notes
1	Supply voltage	V _{CC}	3.6	V	*1
2	Supply current	I _{CC}	20	mA	
3	Power dissipation	P_{D}	50.8	mW	*2
4	Operating ambient temperature	T _{opr}	-30 to +85	°C	*3
5	Storage temperature	T_{stg}	-55 to +125	°C	*3

Notes) *1: The values under the condition not exceeding the above absolute maximum ratings and the power dissipation.

■ Operating Supply Voltage Range

Parameter	Symbol	Range	Unit	Notes
Supply voltage range	V _{CC}	2.7 to 2.875	V	*1

Note) *1: The values under the condition not exceeding the above absolute maximum ratings and the power dissipation.

^{*2 :} The power dissipation shown is the value at $T_a = 85^{\circ}$ C for the independent (unmounted) IC package without a heat sink. When using this IC, refer to the \bullet $P_D - T_a$ diagram in the \blacksquare Technical Data and design the heat radiation with sufficient margin so that the allowable value might not be exceeded based on the conditions of power supply voltage, load, and ambient temperature.

^{*3 :} Except for the power dissipation, operating ambient temperature, and storage temperature, all ratings are for T_a = 25°C.

■ Allowable Current and Voltage Range

Notes) • Allowable current and voltage ranges are limit ranges which do not result in damages to this IC, and IC operation is not guaranteed within these limit ranges.

- Voltage values, unless otherwise specified, are with respect to GND.
- Do not apply external currents or voltages to any pin not specifically mentioned.

Pin No.	Pin name	Rating	Unit	Notes
A1	CNT1	-0.3 to $(V_{CC} + 0.3)$	V	*2
A2	OUT1	-0.3 to $(V_{CC} + 0.3)$	V	*2
A3	OUT2	-0.3 to $(V_{CC} + 0.3)$	V	*2
A4	OUT3	-0.3 to $(V_{CC} + 0.3)$	V	*2
B4	CNT2	-0.3 to $(V_{CC} + 0.3)$	V	*2
C1	IN1	_	V	*1
C2	CNT3	-0.3 to $(V_{CC} + 0.3)$	V	*2
C3	IN2	_	V	*1
C4	IN3	_	V	*1

Notes) *1 : Do not apply more than 0 dBm at high gain mode (5 dBm at low gain mode) to RF input. This is a RF signal input pin. Do not apply DC.

^{*2 :} $(V_{CC} + 0.3)$ V must not be exceeded 3.6 V.

\blacksquare Electrical Characteristics at V $_{\rm CC}$ = 2.80 V

Note) All parameters are specified under T_a = 25°C±2°C unless otherwise specified.

D.N.a	Development	C: mah al	Conditions		Limits			Notes		
B No.	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Notes		
DC elec	DC electrical characteristics									
DC-1	Circuit current HG (2.1 GHz)	IccHSa	$V_{\rm CC}$ current at 2.1 GHz , High-Gain mode. No input signal.	_	3.3	4.25	mA			
DC-2	Circuit current HG (800 MHz)	IccHSb	$V_{\rm CC}$ current at 800 MHz , High-Gain mode. No input signal.	_	3.3	4.25	mA			
DC-3	Circuit current HG (1.7 GHz)	IccHSc	V _{CC} current at 1.7 GHz , High-Gain mode. No input signal.	_	3.3	4.25	mA	_		
DC-4	Circuit current LG (2.1 GHz)	IccLSa	V _{CC} current at 2.1 GHz , Low-Gain mode. No input signal.	_	11	35	μА	_		
DC-5	Circuit current LG (800 MHz)	IccLSb	V _{CC} current at 800 MHz , Low-Gain mode. No input signal.	_	25	50	μА	_		
DC-6	Circuit current LG (1.7 GHz)	IccLSc	V _{CC} current at 1.7 GHz , Low-Gain mode. No input signal.	_	25	50	μA	_		
DC-7	SW voltage (High)	VIHS	_	2.16	_	2.875	V	_		
DC-8	SW voltage (Low)	VILS	_	0	_	0.6	V	_		
DC-9	SW Current (High)	IIHS	Current at SW pin VIHS = 2.9 V	_	10	20	μА	_		
DC-10	SW Current (Low)	IILS	Current at SW pin VILS = 0 V		10	20	μA	_		

\blacksquare Electrical Characteristics (continued) V_{CC} = 2.80 V

Note) All parameters are specified under $T_a = 25^{\circ}C \pm 2^{\circ}C$, fRXa = 2140 MHz, PRXa = -30 dBm, CW unless otherwise specified.

D N =	Davamatar	C: male al	Conditions		Limits		l lmi4	Notes
B No.	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Notes
2.1 GHz	z : LNA AC characteristics (High-g	gain mode / Lo	ow-gain mode)					
A-1	Gain Step	GΔSa	$G\Delta Sa = GHSa - GLSa$	18.2	21.7	23.5	dB	
2.1 GHz	z : LNA AC characteristics (High-g	jain mode)		•	•	•		
A-2	Power gain	GHSa	f1 = fRXa f2 = fRXa - 190 MHz PRX1 = -30 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	15.3	16.7	18.0	dB	
A-3	IIP3	IIP3H1Sa	f1 = fRXa + 10 MHz f2 = fRXa + 20 MHz Input 2 signals (f1, f2)	-10	0	_	dBm	
2.1 GHz	z : LNA AC characteristics (Low-g	ain mode)						
A-4	Power gain	GLSa	f1 = fRXa f2 = fRXa - 190 MHz PRX1 = -24 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	-6.1	-5.0	-4.0	dB	_

\blacksquare Electrical Characteristics (continued) V_{CC} = 2.80 V

Note) All parameters are specified under $T_a = 25^{\circ}C \pm 2^{\circ}C$, fRXb = 881.5 MHz, PRXb = -30 dBm, CW unless otherwise specified.

D No	Doromotor	Cumbal	Conditions		Limits		Unit	Notes
B No.	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	inoles
800 MH	lz : LNA AC characteristics (High-	gain mode / L	.ow-gain mode)					
B-1	Gain Step	GΔSb	$G\Delta Sb = GHSb - GLSb$	18.2	22.2	23.8	dB	_
800 MH	lz : LNA AC characteristics (High-	gain mode)						
B-2	Power gain	GHSb	f1 = fRXb f2 = fRXb - 45 MHz PRX1 = -30 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	15.5	16.7	18.0	dB	
В-3	IIP3	IIP3H1Sb	f1 = fRXb + 10 MHz f2 = fRXb + 20 MHz Input 2 signals (f1, f2)	-10	-5	_	dBm	_
800 MH	اz : LNA AC characteristics (Low-	gain mode)						
B-4	Power gain	GLSb	f1 = fRXb f2 = fRXb - 45 MHz PRX1 = -24 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	-5.9	-5.5	-4.0	dB	

■ Electrical Characteristics (continued) $V_{CC} = 2.80 \text{ V}$

Note) All parameters are specified under $T_a = 25^{\circ}C \pm 2^{\circ}C$, fRXc = 1862.5 MHz, PRXc = -30 dBm, CW unless otherwise specified.

D.N.s	Development	C. mah al	Conditions		Limits		Linit	Notes		
B No.	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Notes		
1.7 GHz	z : LNA AC characteristics (High-g	jain mode / Lo	ow-gain mode)							
C-1	Gain Step	GΔSc	$G\Delta Sc = GHSc - GLSc$	17.9	21.5	23.7	dB	_		
1.7 GHz	z : LNA AC characteristics (High-g	jain mode)								
C-2	Power gain	GHSc	f1 = fRXc f2 = fRXc - 95 MHz PRX1 = -30 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	15.0	16.5	17.8	dB	_		
C-3	IIP3	IIP3H1Sc	f1 = fRXc + 10 MHz f2 = fRXc + 20 MHz Input 2 signals (f1, f2)	-7.5	-3		dBm			
1.7 GHz	1.7 GHz : LNA AC characteristics (Low-gain mode)									
C-4	Power gain	GLSc	f1 = fRXc f2 = fRXc - 95 MHz PRX1 = -24 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	-6.0	-5.0	-4.0	dB	_		

\blacksquare Electrical Characteristics (Reference values for design) at V_{CC} = 2.8 V

Notes) • All characteristics are specified under $T_a = 25^{\circ}C \pm 2^{\circ}C$, fRXa = 2110 MHz to 2170 MHz, PRXa = -30 dBm, CW

• The characteristics listed below are reference values derived from the design of the IC and are not guaranteed by inspection. If a problem does occur related to these characteristics, we will respond in good faith to user concerns.

DNa	Davanatas	Coursells and	Conditions	Refe	rence v	alues	l lait	Notes
B No.	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Notes
2.1 GH:	z : LNA AC characteristics (High	n-gain mode / L	ow-gain mode)					
D-1	Gain Step	GΔa	$G\Delta a = GHa - GLa$	18.2	21.7	23.5	dB	_
D-2	In - band gain deviation	Gch∆a	_	_	_	1.8	dB	_
2.1 GH:	z : LNA AC characteristics (High	n-gain mode)						
D-3	Input VSWR	Vswr_inHa	_		_	2.1		_
D-4	Output VSWR	Vswr_outHa	_	_	_	2.3	_	_
D-5	Power gain	GHa	f1 = fRXa f2 = fRXa – 190 MHz PRX1 = -30 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	15.3	16.7	18.0	dB	_
D-6	Noise figure	NFHa	f1 = fRXa f2 = fRXa – 190 MHz PRX2 = -24 dBm Input 2 signals (f1, f2)	_	1.75	1.95	dB	_
D-7	IIP3	IIP3H1a	f1 = fRXa + 10 MHz f2 = fRXa + 20 MHz Input 2 signals (f1, f2)	-10	0		dBm	_
D-8	Reverse isolation	Ris_H1a	2 .1GHz band Output → 2 .1GHz band input f = 1920 to 2170 MHz		-34	-30	dB	_

\blacksquare Electrical Characteristics (Reference values for design) (continued) at V_{CC} = 2.8 V

Notes) • All characteristics are specified under $T_a = 25^{\circ}C \pm 2^{\circ}C$, fRXa = 2110 MHz to 2170 MHz, PRXa = -30 dBm, CW

• The characteristics listed below are reference values derived from the design of the IC and are not guaranteed by inspection. If a problem does occur related to these characteristics, we will respond in good faith to user concerns.

D Na	Donomoton	Complete al			rence va	nce values		Neter		
B No.	. Parameter Symbol Conditions		Min Typ M		Max	Unit	Notes			
2.1 GH:	2.1 GHz : LNA AC characteristics (Low-gain mode)									
D-9	Input VSWR	Vswr_inLa —		_	_	2.1	_	_		
D-10	Output VSWR	Vswr_outLa	_		_	2.5	_	_		
D-11	Power gain	GLa	f1 = fRXa f2 = fRXa - 190 MHz PRX1 = -24 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	-6.1	-5.0	-4.0	dB			
D-12	Noise figure	NFLa	f1 = fRXa f2 = fRXa - 190 MHz PRX2 = -24 dBm Input 2 signals (f1, f2)	_	5	6.8	dB	_		
D-13	IIP3	f1 = fRXa + 3.5 MHz f2 = fRXa + 6.5 MHz IIP3_LGa PRX1 = -15 dBm PRX2 = -15 dBm Input 2 signals (f1, f2)		2	20	—	dBm	_		
D-14	Reverse isolation	Ris_L1a 2 .1GHz band Output → 2.1 GHz band input		-6.1	-5.0	-4.0	dB	_		

\blacksquare Electrical Characteristics (Reference values for design) (continued) at $V_{CC} = 2.8 \text{ V}$

Notes) • All characteristics are specified under $T_a = 25^{\circ}\text{C} \pm 2^{\circ}\text{C}$, fRXb = 869 MHz to 895 MHz, PRXb = -30 dBm, CW

• The characteristics listed below are reference values derived from the design of the IC and are not guaranteed by inspection. If a problem does occur related to these characteristics, we will respond in good faith to user concerns.

D.N.	Parameter	Cumbal	0 4'#'	Reference values		alues	Unit	Natas	
B No.	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Notes	
800 MHz : LNA AC characteristics (High-gain mode / Low-gain mode)									
E-1	Gain Step	GΔb	$G\Delta b = GHb - GLb$	18.2	22.2	23.8	dB	_	
E-2	In - band gain deviation	Gch∆b	_	_	_	1.8	dB	_	
800 MF	800 MHz : LNA AC characteristics (High-gain mode)								
E-3	Input VSWR	Vswr_inHb	_	_	_	1.8		_	
E-4	Output VSWR	Vswr_outHb	_	_	_	2.0	_	_	
E-5	Power gain	GHb	f1 = fRXb f2 = fRXb - 45 MHz PRX1 = -30 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	15.5	16.7	18.0	dB		
E-6	Noise figure	NFHb	f1 = fRXb f2 = fRXb - 45 MHz PRX2 = -24 dBm Input 2 signals (f1, f2)	_	1.8	2.0	dB	_	
E-7	IIP3	IIP3H1b	f1 = fRXb + 10 MHz f2 = fRXb + 20 MHz Input 2 signals (f1, f2)	-10	-5	_	dBm	_	
E-8	Reverse isolation	Ris_H2b	800 MHz band Output \rightarrow 800 MHz band input $f = 830 \text{ to } 885 \text{ MHz}$	_	-26	-21.5	dB	_	

\blacksquare Electrical Characteristics (Reference values for design) (continued) at $V_{CC} = 2.8 \text{ V}$

Notes) • All characteristics are specified under $T_a = 25^{\circ}\text{C} \pm 2^{\circ}\text{C}$, fRXb = 869 MHz to 895 MHz, PRXb = -30 dBm, CW

• The characteristics listed below are reference values derived from the design of the IC and are not guaranteed by inspection. If a problem does occur related to these characteristics, we will respond in good faith to user concerns.

5.11	Parameter Symbol Conditions	0 1111	Reference value		alues					
B No. Parameter Symbol Co		Conditions	Min	Тур	Max	Unit	Notes			
800 MF	800 MHz : LNA AC characteristics (Low-gain mode)									
E-9	Input VSWR	Vswr_inLb	_	_	_	1.8	_	_		
E-10	Output VSWR	Vswr_outLb	_	_	_	1.8	_	_		
E-11	Power gain	GLb	f1 = fRXb f2 = fRXb - 45 MHz PRX1 = -24 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	-5.9	-5.5	-4.2	dB	_		
E-12	Noise figure	NFLb $ \begin{aligned} f1 &= fRXb \\ f2 &= fRXb - 45 \text{ MHz} \\ PRX2 &= -24 \text{ dBm} \\ Input 2 \text{ signals } (f1, f2) \end{aligned} $		_	5.5	7	dB	_		
E-13	IIP3	IIP3_LGb	f1 = fRXb + 3.5 MHz f2 = fRXb + 6.5 MHz PRX1 = -15 dBm PRX2 = -15 dBm Input 2 signals (f1, f2)	2	20	_	dBm	_		
E-14	Reverse isolation	Ris_L2b	800 MHz band Output → 800 MHz band input	-5.9	-5.5	-4.2	dB	_		

\blacksquare Electrical Characteristics (Reference values for design) (continued) at V_{CC} = 2.8 V

Notes) • All characteristics are specified under $T_a = 25^{\circ}\text{C} \pm 2^{\circ}\text{C}$, fRXc = 1844.9 MHz to 1879.9 MHz, PRXc = -30 dBm, CW

• The characteristics listed below are reference values derived from the design of the IC and are not guaranteed by inspection. If a problem does occur related to these characteristics, we will respond in good faith to user concerns.

B No.	Parameter	Cumbal	Conditions	Reference values			Unit	Notes	
B NO.	Parameter	Symbol	Conditions	Min	Тур	Max	Offic	Notes	
1.7 GH:	z : LNA AC characteristics (High	n-gain mode / L	.ow-gain mode)						
F-1	Gain Step	$G\Delta c$ $G\Delta c = GHc - GLc$		17.9	21.5	23.7	dB	_	
F-2	In - band gain deviation	Gch∆c	_	_	_	1.8	dB	_	
1.7 GH:	1.7 GHz : LNA AC characteristics (High-gain mode)								
F-3	Input VSWR	Vswr_inHc	_	_	_	2.0	_	_	
F-4	Output VSWR	Vswr_outHc	_	_	_	2.1	_	_	
F-5	Power gain	GHc	f1 = fRXc f2 = fRXc - 95 MHz PRX1 = -30 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	15.0	16.5	17.8	dB	_	
F-6	Noise figure	NFHc	f1 = fRXc f2 = fRXc - 95 MHz PRX2 = -24 dBm Input 2 signals (f1, f2)	_	1.65	1.85	dB	_	
F-7	IIP3	ПРЗН1с	f1 = fRXc + 10 MHz f2 = fRXc + 20 MHz Input 2 signals (f1, f2)	-7.5	-3	_	dBm	_	
F-8	Reverse isolation	Ris_H3c	1.7 GHz band Output → 1.7 GHz band input f = 1745 to 1880 MHz	_	-37	-32	dB	_	

\blacksquare Electrical Characteristics (Reference values for design) (continued) at V_{CC} = 2.8 V

Notes) • All characteristics are specified under $T_a = 25^{\circ}\text{C} \pm 2^{\circ}\text{C}$, fRXc = 1844.9 MHz to 1879.9 MHz, PRXc = -30 dBm, CW

• The characteristics listed below are reference values derived from the design of the IC and are not guaranteed by inspection. If a problem does occur related to these characteristics, we will respond in good faith to user concerns.

	Doromotor	Come le el	0 199	Reference values				Notes	
B No.	Parameter	Symbol	Conditions	Min	Тур	Max	Unit	Notes	
1.7 GHz : LNA AC characteristics (Low-gain mode)									
F-9	Input VSWR	Vswr_inLc	vr_inLc —		_	1.8	_	_	
F-10	Output VSWR	Vswr_outLc	_	_	_	2.4	_	_	
F-11	Power gain	GLc	f1 = fRXc f2 = fRXc - 95 MHz PRX1 = -24 dBm PRX2 = -24 dBm Input 2 signals (f1, f2)	-6.0	-5.0	-4.0	dB		
F-12	Noise figure	NFLc	f1 = fRXc f2 = fRXc - 95 MHz PRX2 = -24 dBm Input 2 signals (f1, f2)	_	5.0	6.8	dB	_	
F-13	IIP3	IIP3_LGc	f1 = fRXc + 3.5 MHz f2 = fRXc + 6.5 MHz PRX1 = -15 dBm PRX2 = -15 dBm Input 2 signals (f1, f2)	2.0	20	_	dBm		
F-14	Reverse isolation	Ris_L3c	1.7 GHz band Output → 1.7 GHz band input	-6.0	-5.0	-4.0	dВ	_	

■ Control Pins Mode Table

Note) Control voltage range : See B No. DC-7 / B No. DC-8 $\,$ at $\,$ page 8.

CNT1 (Band Select1) (A1)	CNT2 (Band Select2) (B4)	CNT3 (Gain Control) (C2)	Band1 (2.1 GHz)	Band2 (800 MHz)	Band3 (1.7 GHz)	Mode
T	T	High	High-Gain	Off	Off	2.1 GHz High-Gain
Low	Low	Low	Low-Gain	Off	Off	2.1 GHz Low-Gain
11: -l.	T	High	Off	High-Gain	Off	800 MHz High-Gain
High	Low	Low	Off	Low-Gain	Off	800 MHz Low-Gain
T	II: _1.	High	Off	Off	High-Gain	1.7 GHz High-Gain
Low	High	Low	Off	Off	Low-Gain	1.7 GHz Low-Gain
High	High	_	_	_	_	_

Panasonic

■ Technical Data

• I/O block circuit diagrams and pin function descriptions

Note) The characteristics listed below are reference values derived from the design of the IC and are not guaranteed.

Pin No.	Voltage	Internal Circuit	Description
A1	I	(AI) W GND	2.1 GHz / 800 MHz / 1.7 GHz Band selective SW 1 0.60 V or less : Low 2.16 V or more : High
A2	_	V _{CC} A2 GND	1.7 GHz LNA RF Output
A3	_	Refer to A2	2.1 GHz LNA RF Output
A4	_	Refer to A2	800 MHz LNA RF Output
B1	2.8 V	_	Voltage supply (V _{CC})
В2	0.0 V	_	GND
B4	_	Refer to A1	2.1 GHz / 800 MHz / 1.7 GHz Band selective SW 2 0.60 V or less : Low 2.16 V or more : High

■ Technical Data (continued)

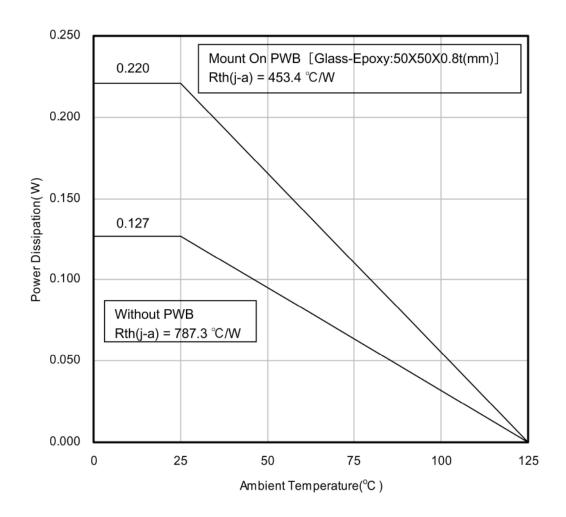
• I/O block circuit diagrams and pin function descriptions (continued)

Note) The characteristics listed below are reference values derived from the design of the IC and are not guaranteed.

Pin No.	Voltage	Internal Circuit	Description
C1	0.75 V	V _{cc} GND	1.7 GHz LNA RF Input
C2	_	Refer to A1	High-Gain / Low-Gain selective SW 0.60 V or less : Low 2.16 V or more : High
С3	0.75 V	Refer to C1	2.1 GHz LNA RF Input
C4	0.75 V	Refer to C1	800 MHz LNA RF Input

■ Technical Data

 \bullet P_D — T_a diagram



■ Usage Notes

- · Special attention and precaution in using
 - 1. This IC is intended to be used for general electronic equipment [UMTS Triple Band handset].
 - Consult our sales staff in advance for information on the following applications:
 - Special applications in which exceptional quality and reliability are required, or if the failure or malfunction of this IC may directly jeopardize life or harm the human body.
 - Any applications other than the standard applications intended.
 - (1) Space appliance (such as artificial satellite, and rocket)
 - (2) Traffic control equipment (such as for automobile, airplane, train, and ship)
 - (3) Medical equipment for life support
 - (4) Submarine transponder
 - (5) Control equipment for power plant
 - (6) Disaster prevention and security device
 - (7) Weapon
 - (8) Others: Applications of which reliability equivalent to (1) to (7) is required

It is to be understood that our company shall not be held responsible for any damage incurred as a result of or in connection with your using the IC described in this book for any special application, unless our company agrees to your using the IC in this book for any special application.

- 2. Pay attention to the direction of LSI. When mounting it in the wrong direction onto the PCB (printed-circuit-board), it might smoke or ignite.
- 3. Pay attention in the PCB (printed-circuit-board) pattern layout in order to prevent damage due to short circuit between pins. In addition, refer to the Pin Description for the pin configuration.
- 4. Perform a visual inspection on the PCB before applying power, otherwise damage might happen due to problems such as a solder-bridge between the pins of the semiconductor device. Also, perform a full technical verification on the assembly quality, because the same damage possibly can happen due to conductive substances, such as solder ball, that adhere to the LSI during transportation.
- 5. Take notice in the use of this product that it might break or occasionally smoke when an abnormal state occurs such as output pin-V_{CC} short (Power supply fault), output pin-GND short (Ground fault), or output-to-output-pin short (load short).
 And, safety measures such as an installation of fuses are recommended because the extent of the above-mentioned damage and smoke emission will depend on the current capability of the power supply.
- 6. When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
 - Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.
- 7. When using the LSI for new models, verify the safety including the long-term reliability for each product.
- 8. When the application system is designed by using this LSI, be sure to confirm notes in this book. Be sure to read the notes to descriptions and the usage notes in the book.
- 9. Due to unshielded structure of this IC, under exposure of light, function and characteristic of the product cannot be guaranteed. During normal operation or even under testing condition, please ensure that IC is not exposed to light.
- 10. Basically, chip surface is ground potential. Please design to ensure no contact between chip surface and metal shielding.

Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products. No license is granted in and to any intellectual property right or other right owned by Panasonic Corporation or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information described in this book.
- (3) The products described in this book are intended to be used for general applications (such as office equipment, communications equipment, measuring instruments and household appliances), or for specific applications as expressly stated in this book.

 Consult our sales staff in advance for information on the following applications:
 - Special applications (such as for airplanes, aerospace, automotive equipment, traffic signaling equipment, combustion equipment, life support systems and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
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- (4) The products and product specifications described in this book are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most up-to-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
 - Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS, thermal stress and mechanical stress) at the time of handling, mounting or at customer's process. When using products for which damp-proof packing is required, satisfy the conditions, such as shelf life and the elapsed time since first opening the packages.
- (7) This book may be not reprinted or reproduced whether wholly or partially, without the prior written permission of our company.

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